CSD18534KCS 60V N 沟道 NexFET™ 功率 MOSFET

1 特性

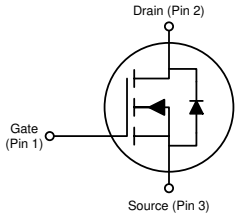
- 超低 Q_g 和 Q_{gd}
- 低热阻
- 雪崩级
- 逻辑电平
- 无铅端子镀层
- 符合 RoHS
- 无卤素
- TO-220 塑料封装

2 应用

- 直流/直流转换
- 次级侧同步整流器
- 电机控制

3 说明

这款 7.6mΩ、60V、TO-220 NexFET™ 功率 MOSFET 旨在用于更大限度地降低功率转换应用中的损耗。



产品概要

T_A = 25°C		典型值		单位
V_{DS}	漏源电压	60		V
Q_g	栅极电荷总量 (10V)	19		nC
Q_{gd}	栅极电荷（栅极到漏极）	3.1		nC
$R_{DS(on)}$	漏源导通电阻	V_{GS} = 4.5V	10.2	mΩ
		V_{GS} = 10V	7.6	mΩ
$V_{GS(th)}$	阈值电压	1.9		V

订购信息(1)

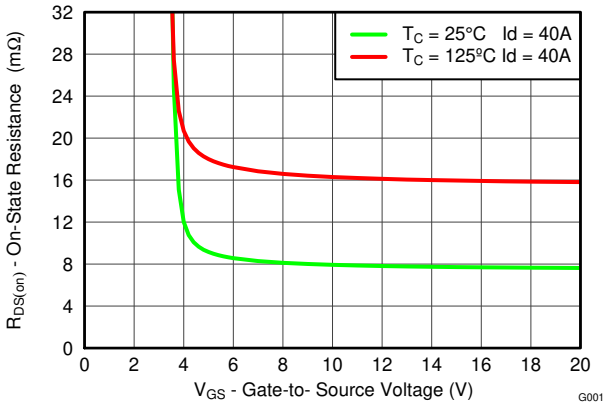
器件	封装	介质	数量	运输
CSD18534KCS	TO-220 塑料封装	管装	50	管装

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

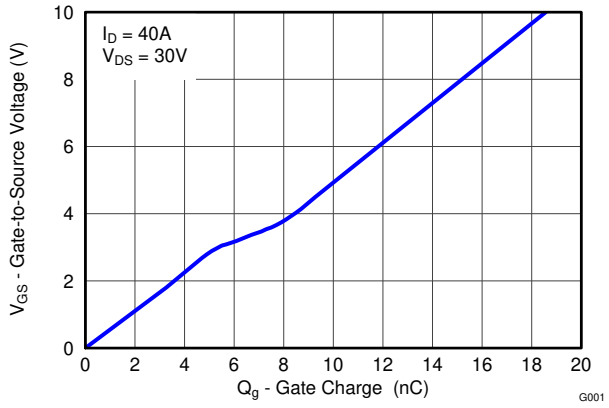
绝对最大额定值

T_A = 25°C		值	单位
V_{DS}	漏源电压	60	V
V_{GS}	栅源电压	±20	V
I_D	持续漏极电流（受封装限制）	100	A
	持续漏极电流（受芯片限制），T_C = 25°C 时测得	73	
	持续漏极电流（受芯片限制），T_C = 100°C 时测得	52	
I_{DM}	脉冲漏极电流(1)	164	A
P_D	功率耗散	107	W
T_J、T_{stg}	工作结温和贮存温度范围	-55 至 175	°C
E_{AS}	雪崩能量，单脉冲 I_D = 38A，L = 0.1mH，R_G = 25Ω	72	mJ

(1) 最大 $R_{\theta JC}$ = 1.3°C/W，脉冲持续时间 ≤ 100μs，占空比 ≤ 1%



$R_{DS(on)}$ 与 V_{GS} 之间的关系



栅极电荷

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4 Specifications

4.1 Electrical Characteristics

T_A = 25°C unless otherwise stated

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0V, I_D = 250 μA	60			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0V, V_{DS} = 48V			1	μA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	1.5	1.9	2.3	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 4.5V, I_D = 40A		10.2	13.3	mΩ
		V_{GS} = 10V, I_D = 40A		7.6	9.5	mΩ
g_{fs}	Transconductance	V_{DS} = 30V, I_D = 40A		100		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz		1500	1880	pF
C_{oss}	Output Capacitance			164	205	pF
C_{rss}	Reverse Transfer Capacitance			5.0	6.5	pF
R_G	Series Gate Resistance			1.5	3.0	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 30V, I_D = 40A		9.3	12	nC
Q_g	Gate Charge Total (10V)			19	24	nC
Q_{gd}	Gate Charge Gate-to-Drain			3.1		nC
Q_{gs}	Gate Charge Gate-to-Source			4.8		nC
$Q_{g(th)}$	Gate Charge at V_{th}			3.3		nC
Q_{oss}	Output Charge	V_{DS} = 30V, V_{GS} = 0V		18		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 30V, V_{GS} = 10V, I_{DS} = 40A, R_G = 0Ω		4.2		ns
t_r	Rise Time			4.8		ns
$t_{d(off)}$	Turn Off Delay Time			10.4		ns
t_f	Fall Time			2.4		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 40A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 30V, I_F = 40A, di/dt = 300A/μs		68		nC
t_{rr}	Reverse Recovery Time			49		ns

4.2 Thermal Information

T_A = 25°C unless otherwise stated

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	

4.3 Typical MOSFET Characteristics

T_A = 25°C, unless otherwise stated

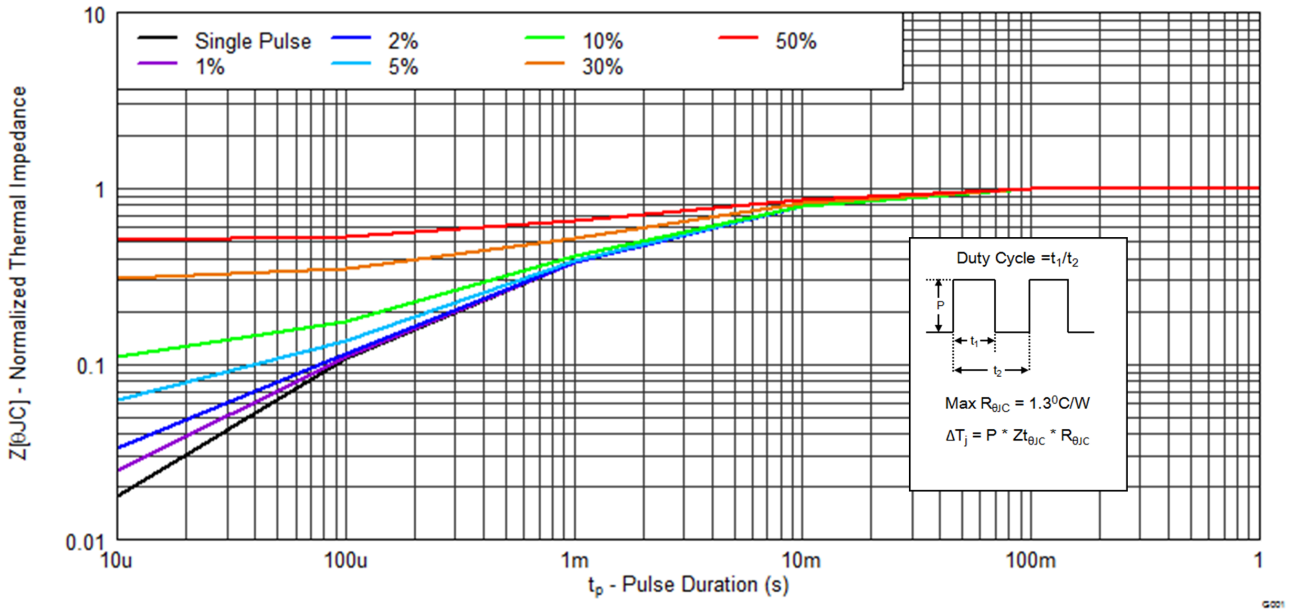

图 4-1. Transient Thermal Impedance

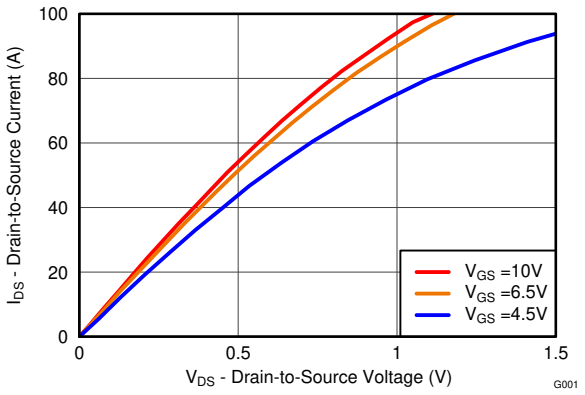

图 4-2. Saturation Characteristics

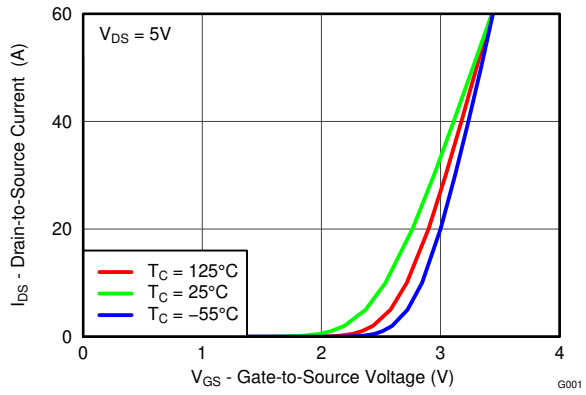

图 4-3. Transfer Characteristics

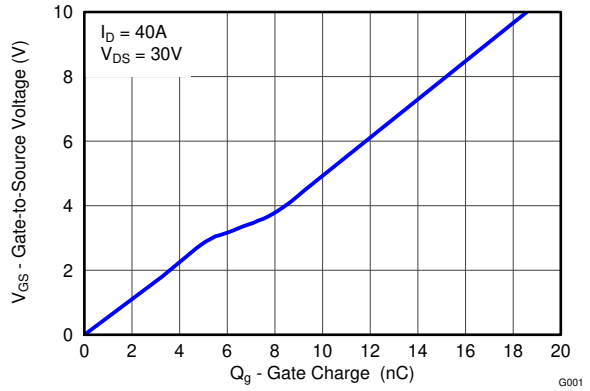

图 4-4. Gate Charge

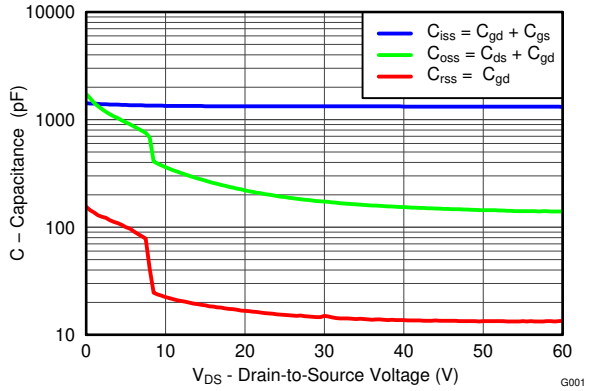

图 4-5. Capacitance

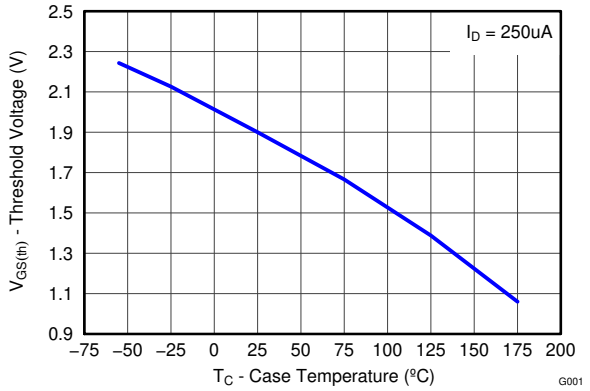

图 4-6. Threshold Voltage vs Temperature

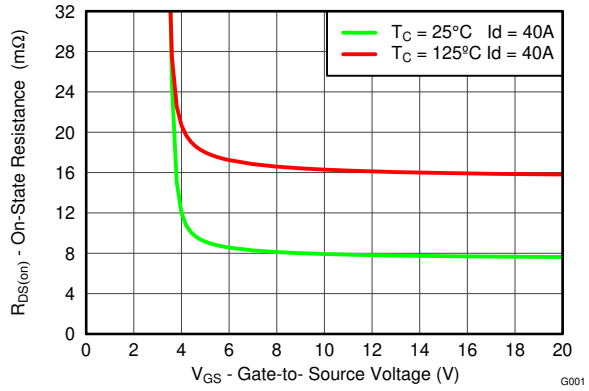

图 4-7. On-State Resistance vs Gate-to-Source Voltage

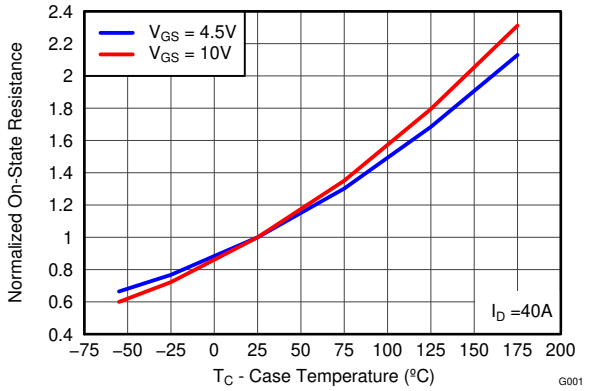

图 4-8. Normalized On-State Resistance vs Temperature

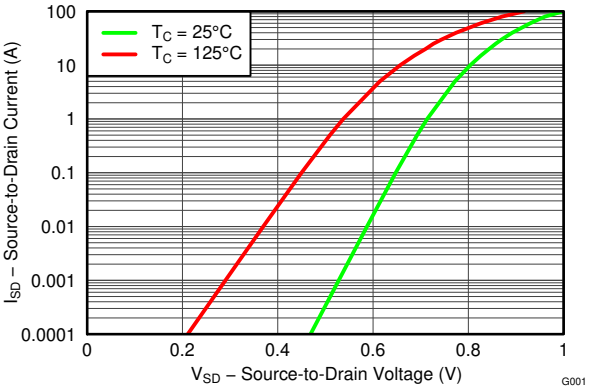

图 4-9. Typical Diode Forward Voltage

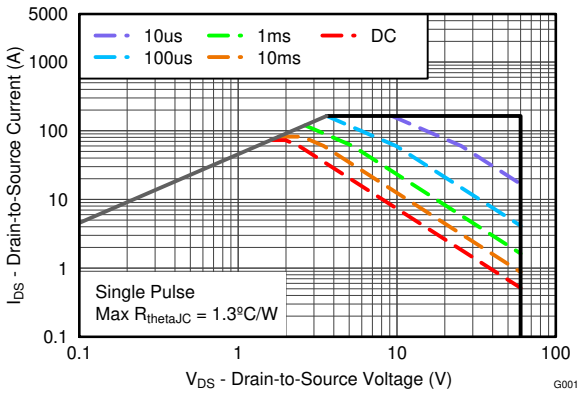

图 4-10. Maximum Safe Operating Area

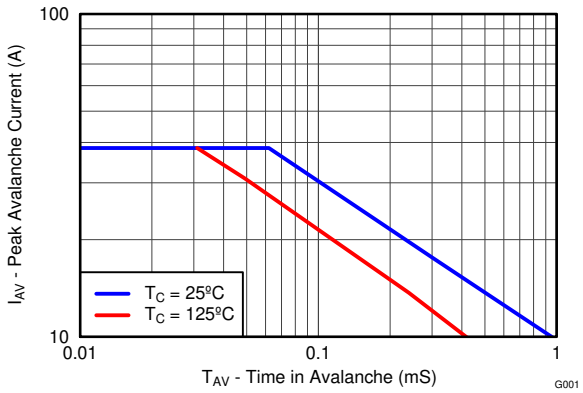

图 4-11. Single Pulse Unclamped Inductive Switching

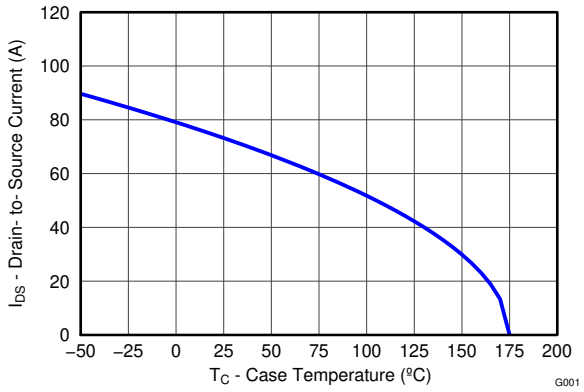

图 4-12. Maximum Drain Current vs Temperature

5 Device and Documentation Support

5.1 第三方产品免责声明

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5.3 支持资源

TI E2E™ 中文支持论坛是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

5.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

6 Revision History

Changes from Revision B (October 2014) to Revision C (March 2024) **Page**

- 更新了整个文档中的表格、图和交叉参考的编号格式 1

Changes from Revision A (April 2014) to Revision B (October 2014) **Page**

- 将 I_{DM} 增加至 164A 1
- 更新了脉冲电流条件 1
- Updated 图 4-1 from a normalized $R_{\theta JA}$ to a normalized $R_{\theta JC}$ curve 4
- Updated the SOA in 图 4-10 4

Changes from Revision A (April 2014) to Revision B (October 2014) **Page**

- 将 I_{DM} 增加至 164A 1
- 更新了脉冲电流条件 1
- Updated 图 4-1 from a normalized $R_{\theta JA}$ to a normalized $R_{\theta JC}$ curve 4
- Updated the SOA in 图 4-10 4

Changes from Revision * (September 2012) to Revision A (April 2014) **Page**

- 更新了文档标题 1
- 更新了说明 1
- 调整了电流，以在“绝对最大额定值”中反映能承受更高的温度 1
- 调整了最大功率，以在“绝对最大额定值”中反映能承受更高的温度 1
- 将“绝对最大额定值”中的最大温度增加至 175ºC 1
- Updated 图 4-6 to extend to 175°C 4
- Updated 图 4-8 to extend to 175°C 4
- Updated 图 4-12 to extend to 175°C 4

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD18534KCS	ACTIVE	TO-220	KCS	3	50	RoHS-Exempt & Green	SN	N / A for Pkg Type	-55 to 175	CSD18534KCS	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

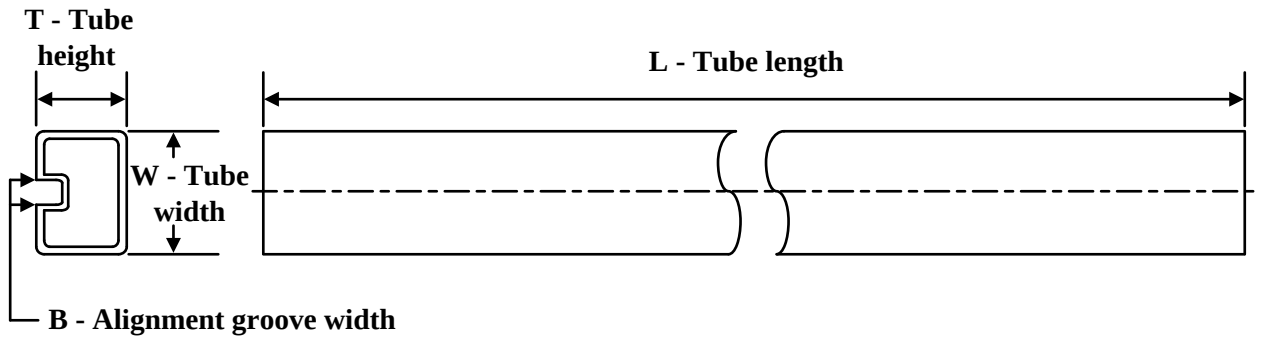
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CSD18534KCS	KCS	TO-220	3	50	532	34.1	700	9.6
CSD18534KCS	KCS	TO-220	3	50	532	34.1	700	9.6

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